Notice of References Cited

Application/Control No. 10/047,323

Q.

Applicant(s)/Patent Under Reexamination LAMPERT ET AL.

Art Unit 1765

Page 1 of 1

U.S. PATENT DOCUMENTS

Examiner

Matthew J Song

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	А	US-5,620,512	04-1997	Gruen et al.	117/108
	В	US-6,270,573	08-2001	Kitabatake et al.	117/95
	С	US-3,949,119	04-1976	Shewchun et al.	117/106
	D	US-5,915,194	06-1999	Powell et al.	438/478
	E	US-3,385,723	05-1968	Pickar	427/228
	F	US-6,193,797	02-2001	Shiomi et al.	117/88
	G	US-5,985,356	11-1999	Schultz et al.	427/8
	Н	US-6,273,950	08-2001	Kitabatake, Makoto	117/95
	ı	US-			
	J	US-			
	к	US-			
	L	US-			
	М	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	0					
	Р					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Fissel et al. "Low temperature growth of SiC Thin Films on Si and 6H-SiC by solid source molecular beam epitaxy" Applied Physics Letters, Vol. 66 No. 23, pp 3182-3184, June 5, 1995, American Institute of Physics.
	V	
	w	
	х	

A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).) Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.